

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA15N120ANTD	FGA15N120ANTD	TO-3P	--	--	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	3	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 250	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 15mA, V _{CE} = V _{GE}	4.5	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 15A, V _{GE} = 15V	--	1.9	2.4	V
		I _C = 15A, V _{GE} = 15V, T _C = 125°C	--	2.2	--	V
		I _C = 30A, V _{GE} = 15V	--	2.3	--	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	2650	--	pF
C _{oes}	Output Capacitance		--	143	--	pF
C _{res}	Reverse Transfer Capacitance		--	96	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	160	--	ns
t _f	Fall Time		--	100	180	ns
E _{on}	Turn-On Switching Loss		--	3	4.5	mJ
E _{off}	Turn-Off Switching Loss		--	0.6	0.9	mJ
E _{ts}	Total Switching Loss		--	3.6	5.4	mJ
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	170	--	ns
t _f	Fall Time		--	150	--	ns
E _{on}	Turn-On Switching Loss		--	3.2	4.8	mJ
E _{off}	Turn-Off Switching Loss		--	0.8	1.2	mJ
E _{ts}	Total Switching Loss		--	4.0	6.0	mJ
Q _g	Total Gate Charge	V _{CE} = 600 V, I _C = 15A, V _{GE} = 15V	--	120	180	nC
Q _{ge}	Gate-Emitter Charge		--	16	22	nC
Q _{gc}	Gate-Collector Charge		--	50	65	nC

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _{FM}	Diode Forward Voltage	I _F = 15A	T _C = 25°C	--	1.7	2.7	V
			T _C = 125°C	--	1.8	--	
t _{rr}	Diode Reverse Recovery Time	I _F = 15A dI/dt = 200 A/μs	T _C = 25°C	--	210	330	ns
			T _C = 125°C	--	280	--	
I _{rr}	Diode Peak Reverse Recovery Cur- rent		T _C = 25°C	--	27	40	A
			T _C = 125°C	--	31	--	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	--	2835	6600	nC
			T _C = 125°C	--	4340	--	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

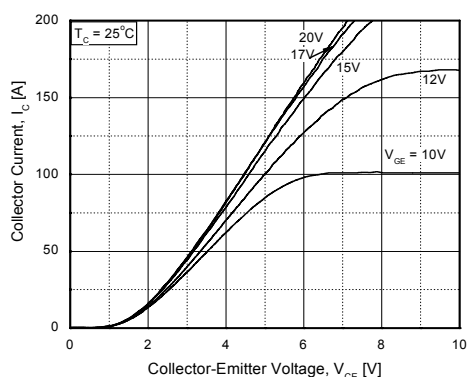


Figure 2. Typical Saturation Voltage Characteristics

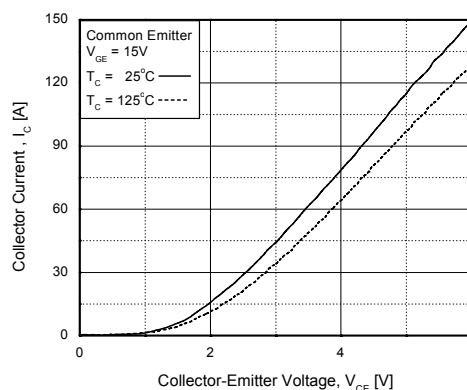


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

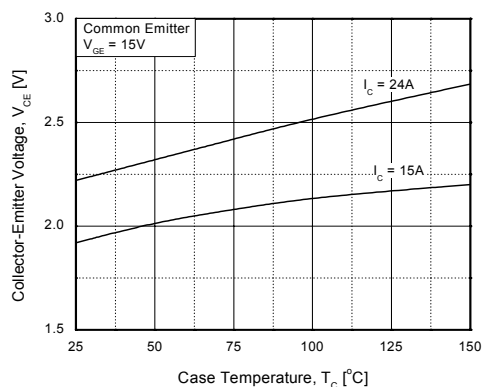


Figure 4. Saturation Voltage vs. V_GE

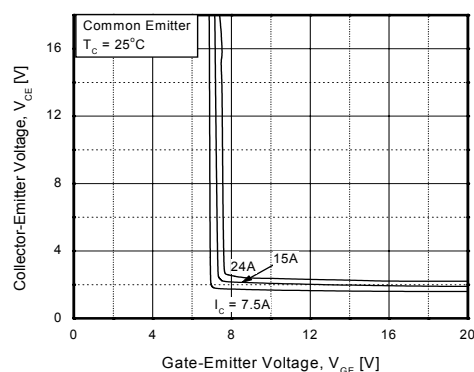


Figure 5. Saturation Voltage vs. V_GE

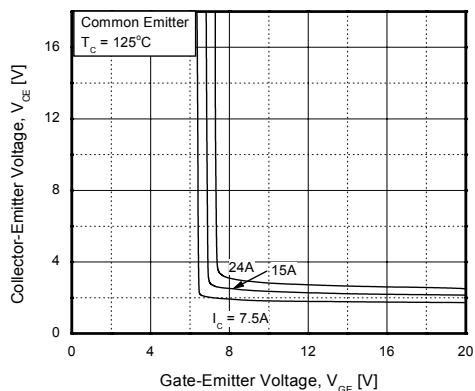
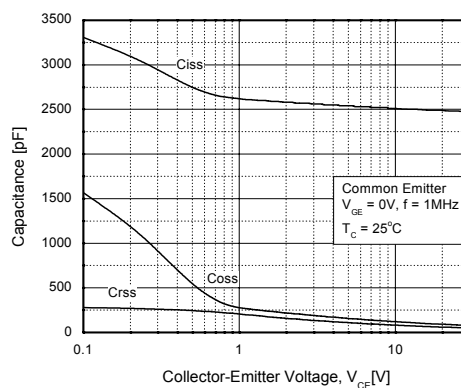


Figure 6. Capacitance Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Turn-On Characteristics vs. Gate Resistance

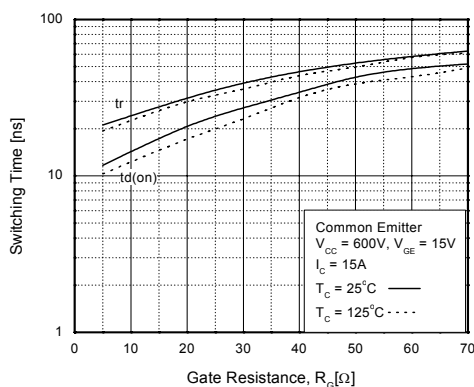


Figure 8. Turn-Off Characteristics vs. Gate Resistance

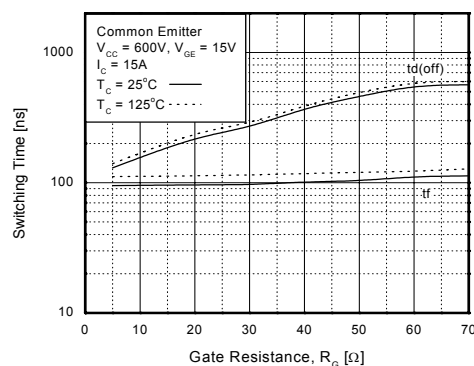


Figure 9. Switching Loss vs. Gate Resistance

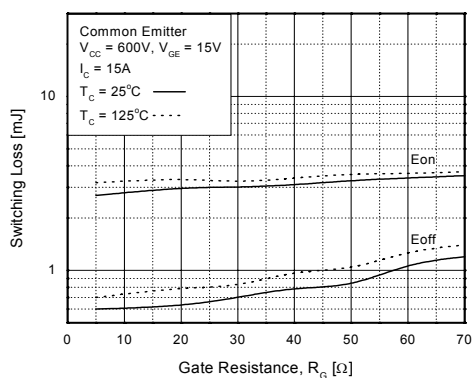


Figure 10. Turn-On Characteristics vs. Collector Current

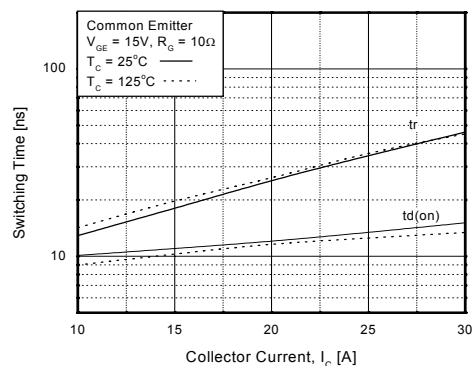


Figure 11. Turn-Off Characteristics vs. Collector Current

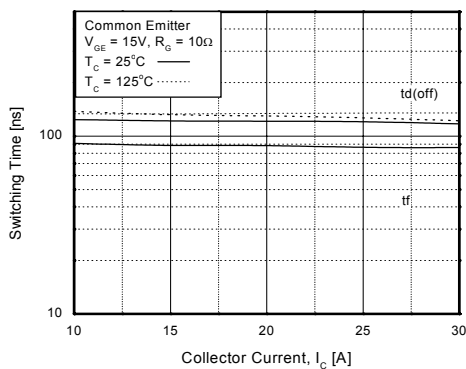
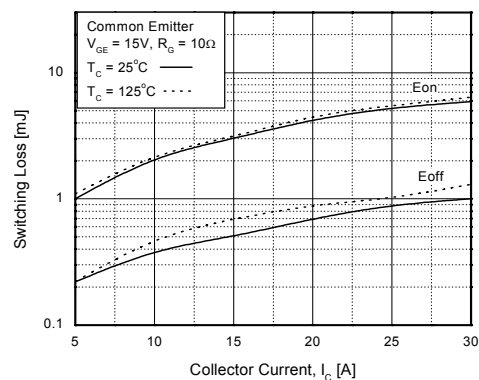


Figure 12. Switching Loss vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Gate Charge Characteristics

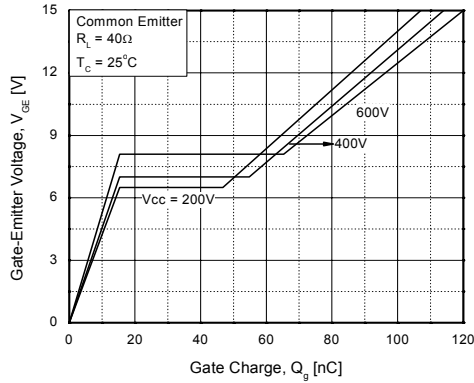


Figure 14. SOA Characteristics

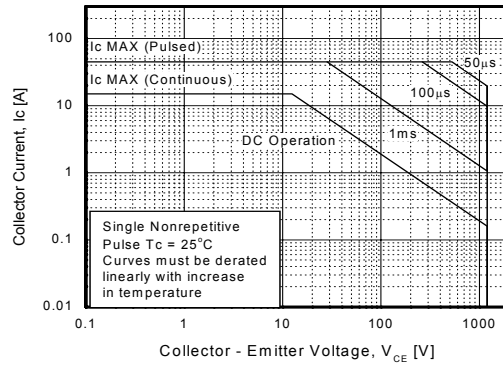


Figure 15. Turn-Off SOA

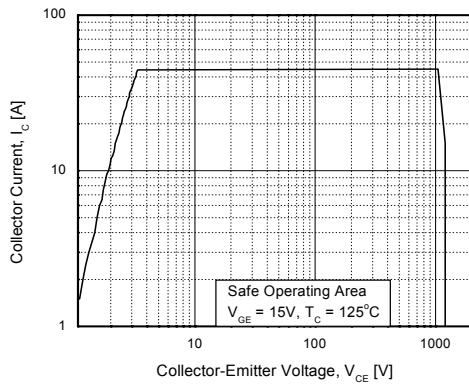
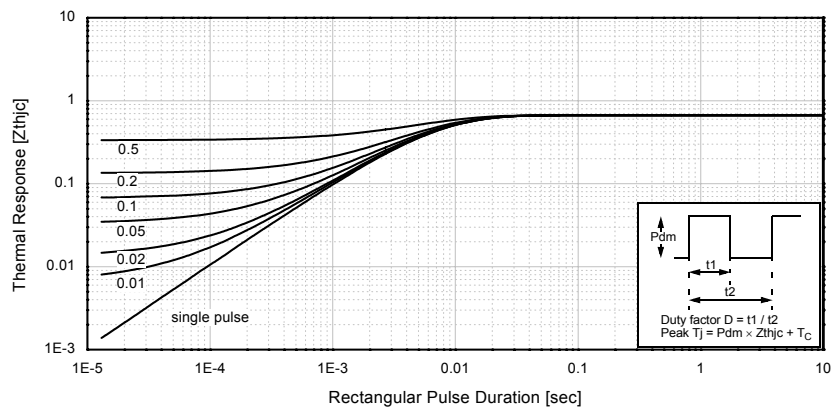


Figure 16. Transient Thermal Impedance of IGBT



Typical Performance Characteristics (Continued)

Figure 17. Forward Characteristics

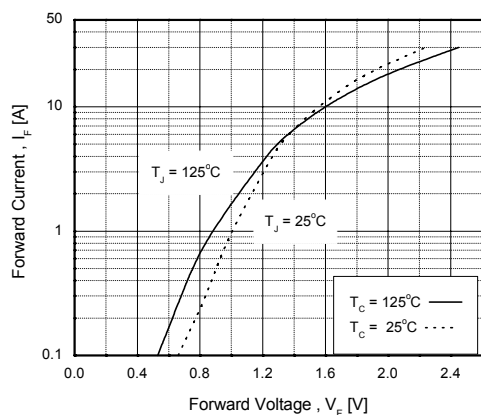


Figure 18. Reverse Recovery Current

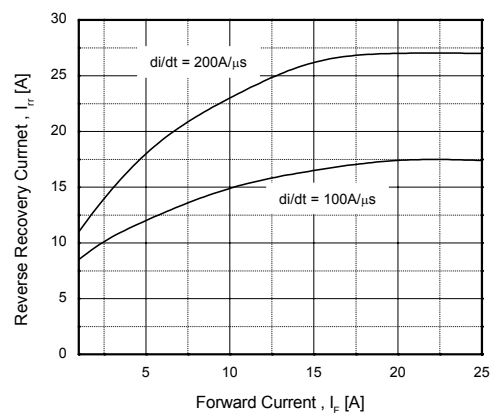


Figure 19. Stored Charge

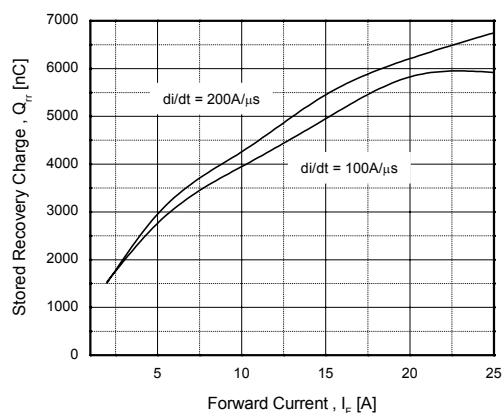
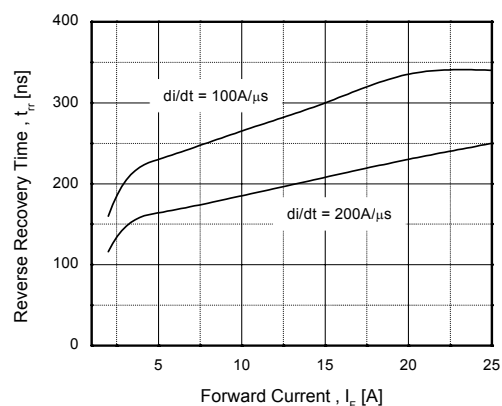
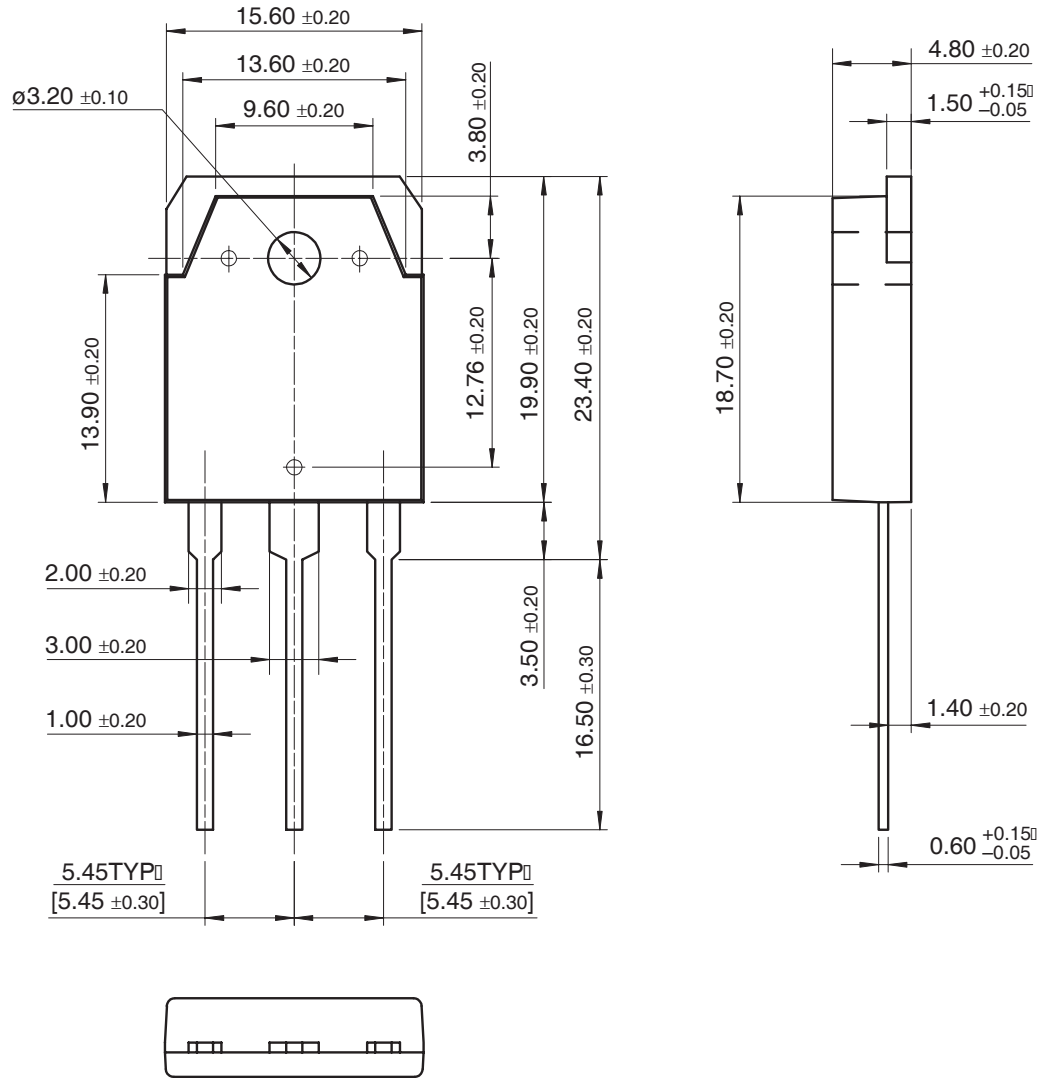


Figure 20. Reverse Recovery Time



Mechanical Dimensions

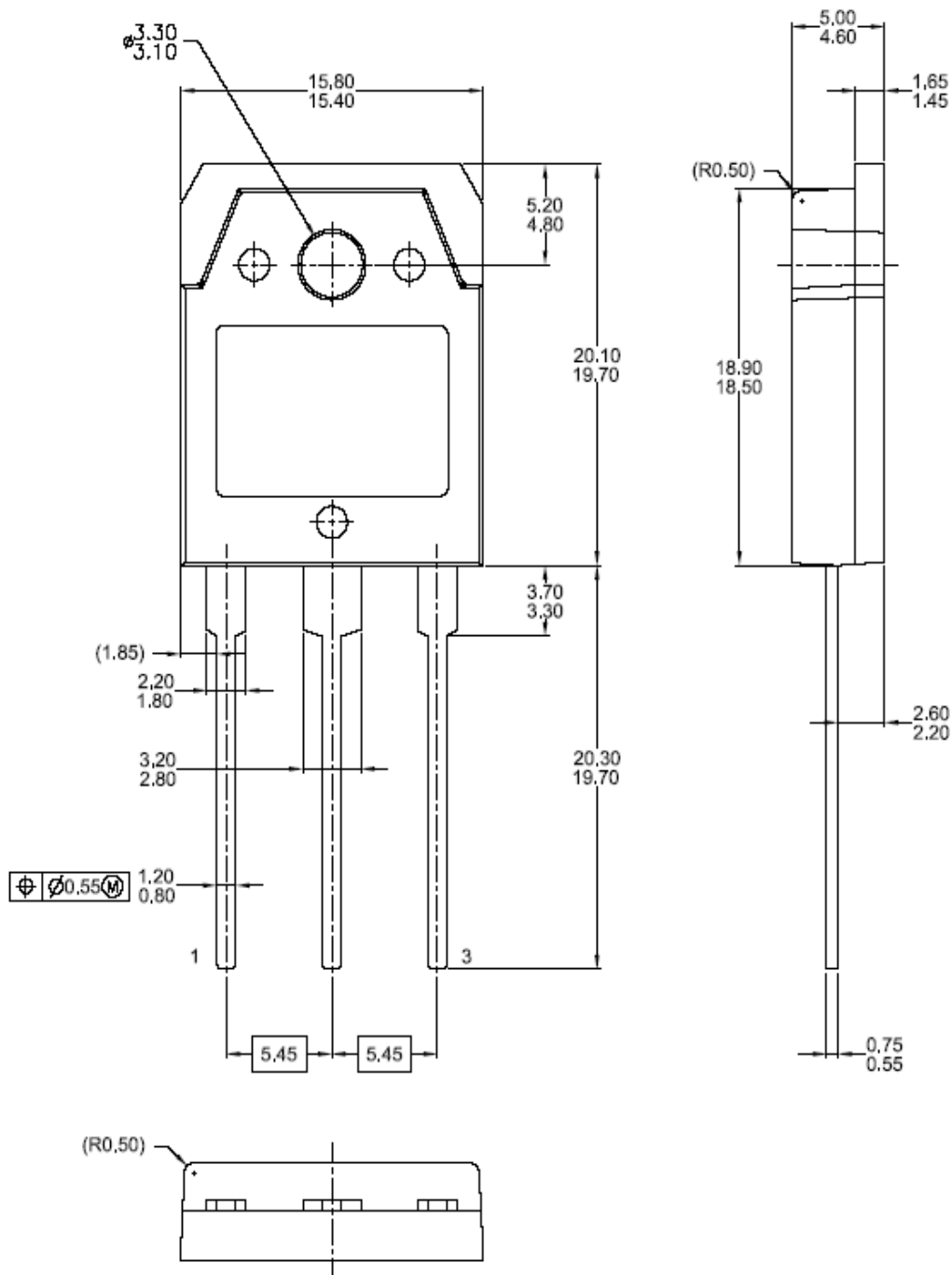
TO-3P



Dimensions in Millimeters

Mechanical Dimensions (continued)

TO-3PN



Dimensions in Millimeters

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